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2. An apparatus according to claim 1, wherein the bottom of the chamber is substantially formed by a glass substrate.
 3. An apparatus according to claim 2, wherein the electrodes are provided on the glass substrate, and are embedded in an insulation layer provided on the glass substrate.
 4. An apparatus according to claim 3, wherein the upright side walls are formed by etching insulation material provided on the insulation layer.
 5. An apparatus according to claim 1, wherein the bottom of the chamber is substantially formed by a silicon wafer.
 6. An apparatus according to claim 5, wherein the silicon wafer is provided with a first insulation layer.
 7. An apparatus according to claim 6, wherein the electrodes are provided on the first insulation layer of the silicon wafer and are embedded in a second insulation layer, which is provided on the first insulation layer.
 8. An apparatus according to claim 7, wherein the upright side walls are formed by etching insulation material provided on the second insulation layer.
 9. An apparatus according to claim 1, wherein the volume of said at least one chamber is maximally 2 nanolitres.
 10. An apparatus according to claim 1, wherein said apparatus comprises a plurality of chambers arranged in an array.

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11. An apparatus according to claim 1, wherein said apparatus is connected to an alternating voltage source having a frequency of at least approximately 15 kHz.

Add ✓ new claims 13-14 as follows:

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12. An apparatus according to claim 6, wherein said first insulation layer comprises SiO_2 .

13. An apparatus according to claim 7, wherein said second insulation layer comprises Si_xN_y .